

Wednesday 6 June

16:00

Technology

Session | Location: No 239 Zhang Heng Road, Pudong New District, 201203, Shanghai, P. R. China | Convener: Dr Nuria Catalan Lasheras

16:00-16:25 High-gradient system integration

Speaker

Carlo Rossi

16:25-16:50

Development and Processing of C-band accelerating structure fabrication for **SXFEL**

Speaker

Hui Wang

16:50-17:15 New directions in structure and component fabrication

Speaker

Kamil Tomasz Szypula

17:15-17:40 R&D Studies on the S-band Hybrid Bunching-accelerating Structure

Speaker

Dr Shilun Pei

High Power RF Source Activities at IHEP 17:40-18:05

Speaker

Dr Zusheng Zhou

18:05-18:30

High Efficiency, High Power, Lower Voltage MBK BAC-TCC Technology Covering X/C/ S-Band

Speaker

Mr Daniel Lundberg

18:30